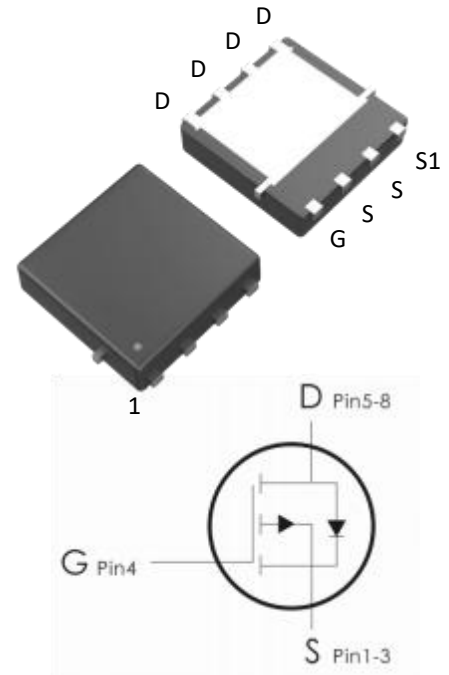


Description:

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge. It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=-40V, I_D=-40A, R_{DS(ON)}<14m\ \Omega @V_{GS}=-10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.
- 6) MSL3



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
SIS443DN-T1-GE3	SIS443DN	DFN3*3-8	5000 pcs/Reel

Absolute Maximum Ratings: ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-40	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	-40	A
	Continuous Drain Current- $T_c=100^\circ\text{C}$	-27	
I_{DM}	Pulsed Drain Current ¹	-180	
P_D	Power Dissipation	52	W
E_{AS}	Single pulse avalanche energy ²	100	mJ
T_j, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ\text{C}$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	3.1	$^\circ\text{C}/\text{W}$

Electrical Characteristics: (T_c=25 °C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250 μA	-30	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =-30V	---	---	-1	μA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0A	---	---	±100	nA
On Characteristics						
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μA	-1	-1.6	-2.5	V
R _{DS(ON)}	Drain-Source On Resistance ³	V _{GS} =-10V, I _D =-15A	---	9	14	m Ω
		V _{GS} =-4.5V, I _D =-10A	---	14	19	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-20V, V _{GS} =0V, f=1MHz	---	3119	---	pF
C _{oss}	Output Capacitance		---	270	--	
C _{rss}	Reverse Transfer Capacitance		---	215	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =-20V, I _D =-11A, R _{ENG} =2.5 Ω, V _{GS} =-10V	---	10.5	---	ns
t _r	Rise Time		---	21	---	ns
t _{d(off)}	Turn-Off Delay Time		---	53	---	ns
t _f	Fall Time		---	29	---	ns
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-20V, I _D =-11A	---	41	---	nC
Q _{gs}	Gate-Source Charge		---	6.5	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	7.6	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _{SD} =-30A	---	---	1.2	V
I _S	Continuous Drain Current	V _D =V _G =0V	---	---	-40	A
I _{SM}	Pulsed Drain Current		---	---	-180	A
T _{rr}	Reverse Recovery Time	I _F =-11A,	---	35	---	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/us	---	40	---	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=-15\text{V}$, $V_G=10\text{V}$, $L=0.5\text{mH}$
3. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, $D_{ut} \leq 0.5\%$

Test Circuit

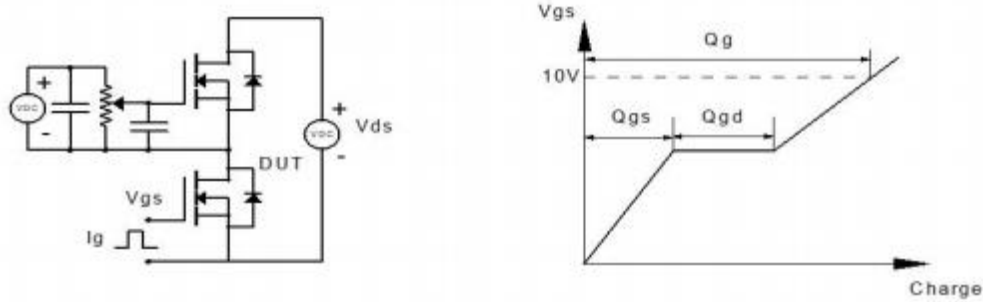


Figure 1: Gate Charge Test Circuit & Waveform

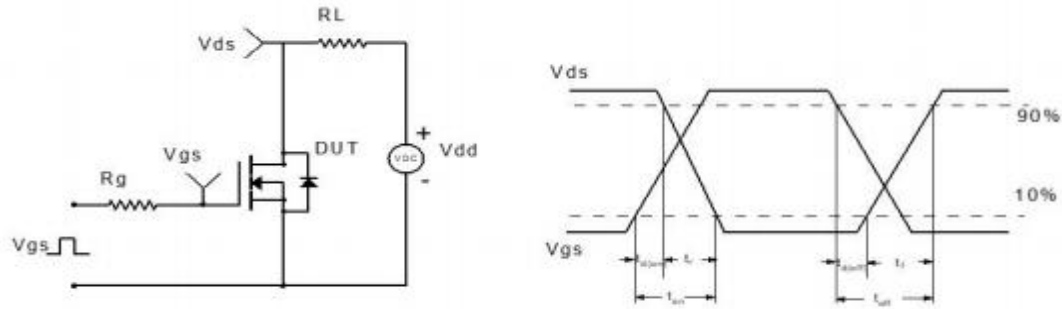


Figure 2: Resistive Switching Test Circuit & Waveform

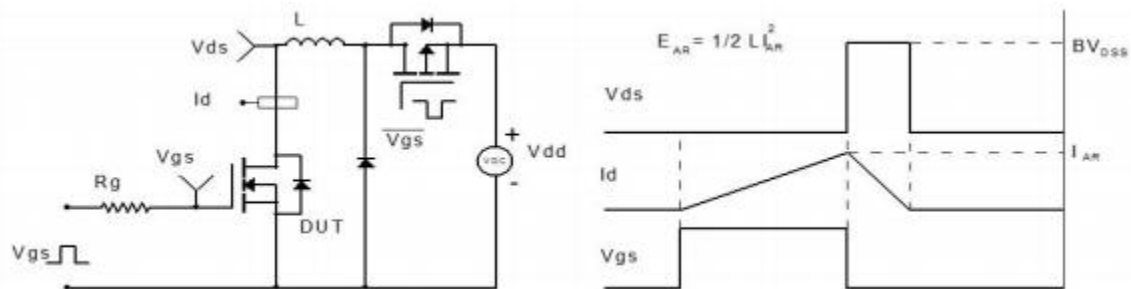


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

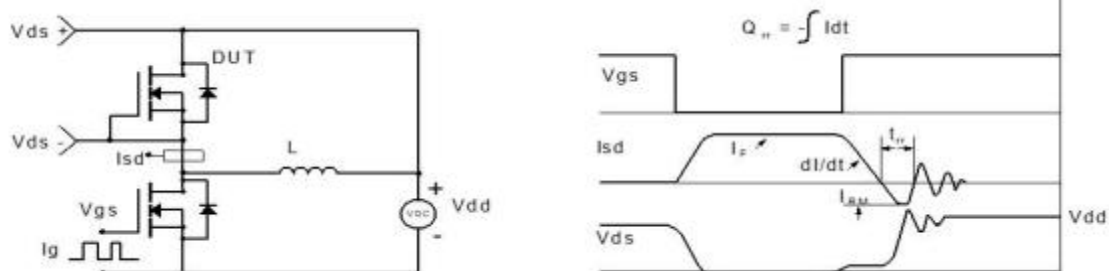
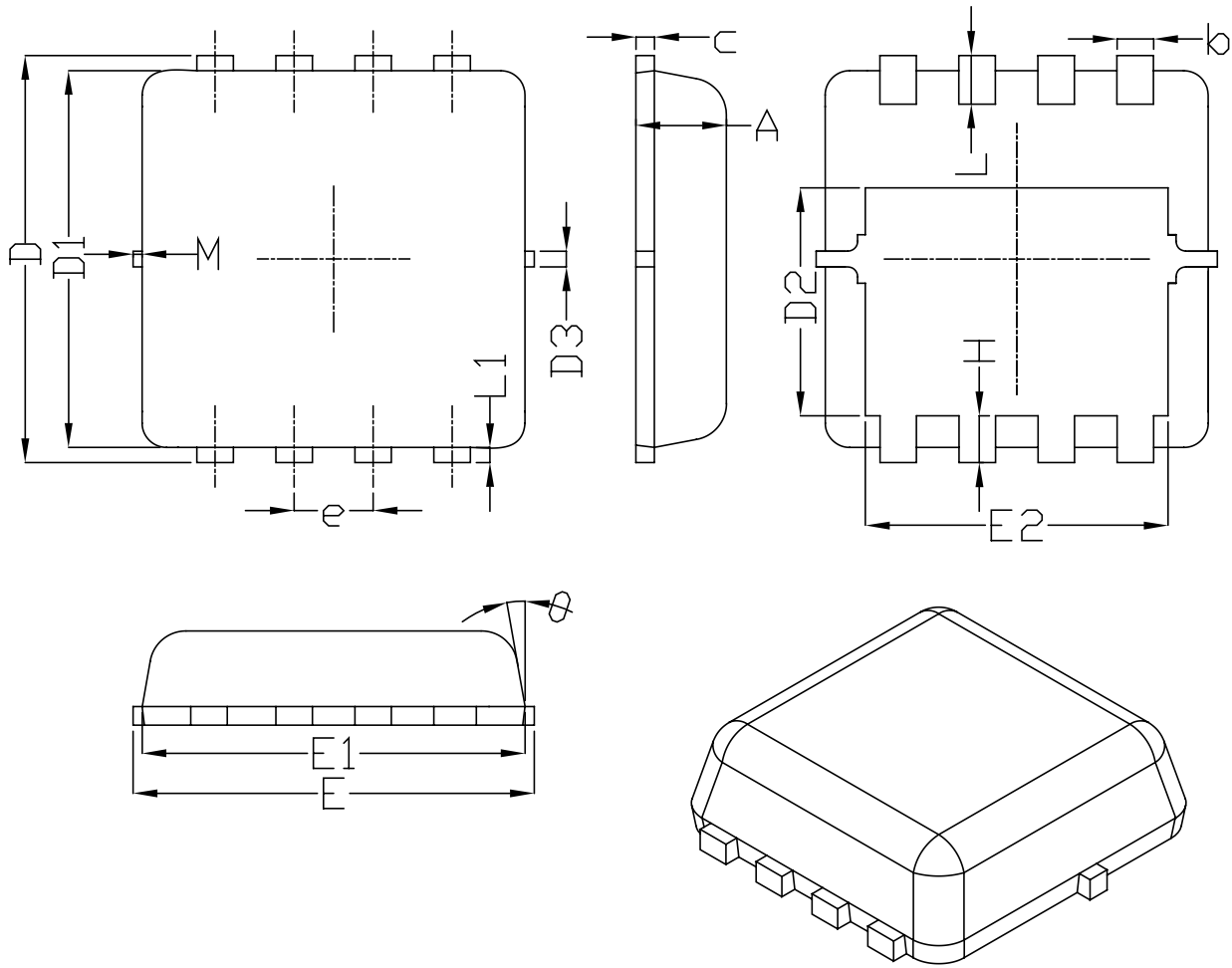
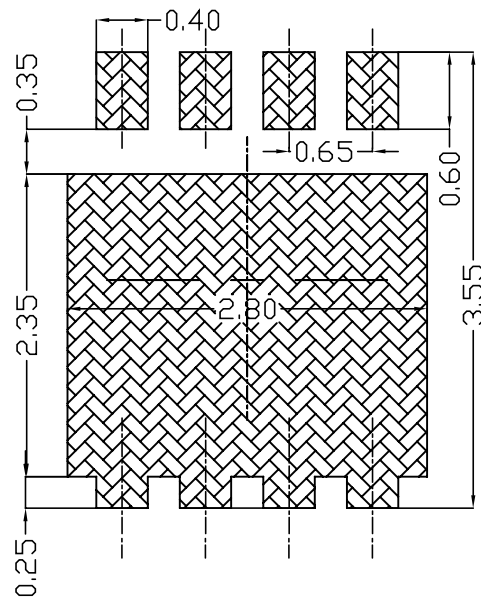


Figure 4: Diode Recovery Test Circuit & Waveform

DFN3X3-8 Package Information:



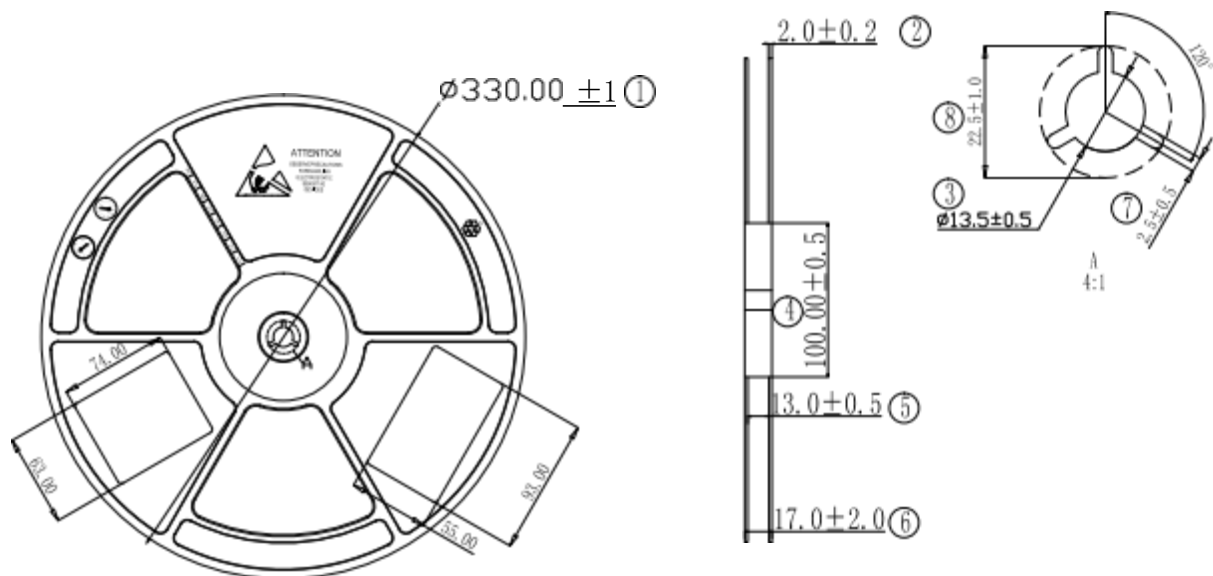
SYMBOL	DIMENSIONAL REOMTS		
	MIN	NOM	MAX
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	---	0.13	---
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	---	0.13	---
θ	---	10°	12°
M	*	*	0.15
* Not specified			



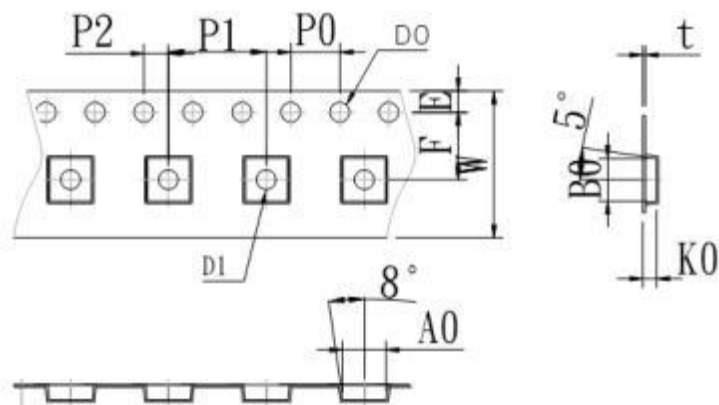
UNIT : mm

Tape & Reel Information

Dimensions in mm



Symbol	A0	B0	K0	D0	D1	P0	P1	10*P0
Spec	3.55±0.10	3.45±0.10	1.13±0.10	1.55±0.10	1.55±0.10	4.00±0.10	8.00±0.10	40.0±0.10
Symbol	W	E	F	P2	t			
Spec	12.00±0.10	1.75±0.10	5.50±0.10	2.00±0.10	0.20±0.05			



Pulling direction